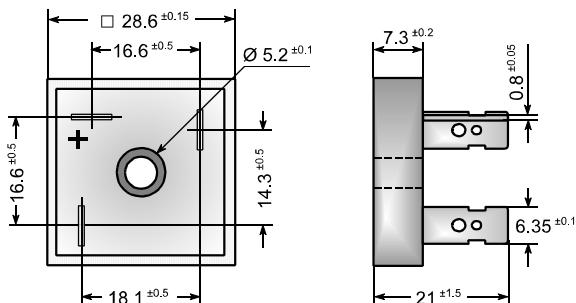
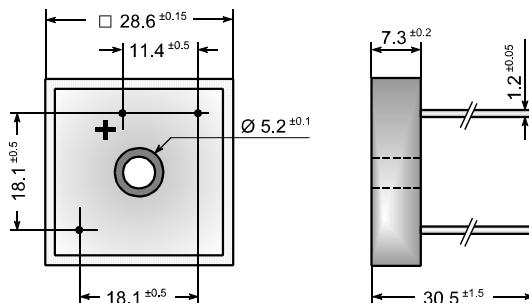


Silicon-Twin Rectifiers
 Center tap

Silizium-Doppeldioden
 Mittelpunktschaltung

Type "F"

Type "W"


Dimensions / Maße in mm

 Nominal current – Nennstrom 30 A

 Alternating input voltage – Eingangswechselspannung 60...250 V

 Dimensions – Abmessungen 28.6 x 28.6 x 7.3 [mm]
 Weight approx. / Gewicht ca.23 g

 Plastic case with alu-bottom
 Casting compound has UL classification 94V-0
 Standard packaging: bulk

 Kunststoffgehäuse mit Alu-Boden
 Vergußmasse UL94V-0 klassifiziert
 Standard Lieferform: lose im Karton

Maximum ratings
Grenzwerte

Type Typ	Alternating input voltage Eingangswechselspann. V_{VRMS} [V]	Rep. peak reverse voltage Period. Spitzensperrspann. V_{RRM} [V] ¹⁾	Surge peak reverse voltage Stoßspitzensperrspannung V_{RSM} [V] ¹⁾
D30 VC20 F/W	60	200	200
D30 VC40 F/W	120	400	400
D30 VC60 F/W	190	600	600
D30 VC80 F/W	250	800	800

 Repetitive peak forward current
 Periodischer Spitzenstrom $f > 15 \text{ Hz}$ I_{FRM} 80 A²⁾

 Peak forward surge current, 50 Hz half sine-wave
 Stoßstrom für eine 50 Hz Sinus-Halbwelle $T_A = 25/C$ I_{FSM} 300 A

 Rating for fusing – Grenzlastintegral, $t < 10 \text{ ms}$ $T_A = 25/C$ i^2t 450 A²s

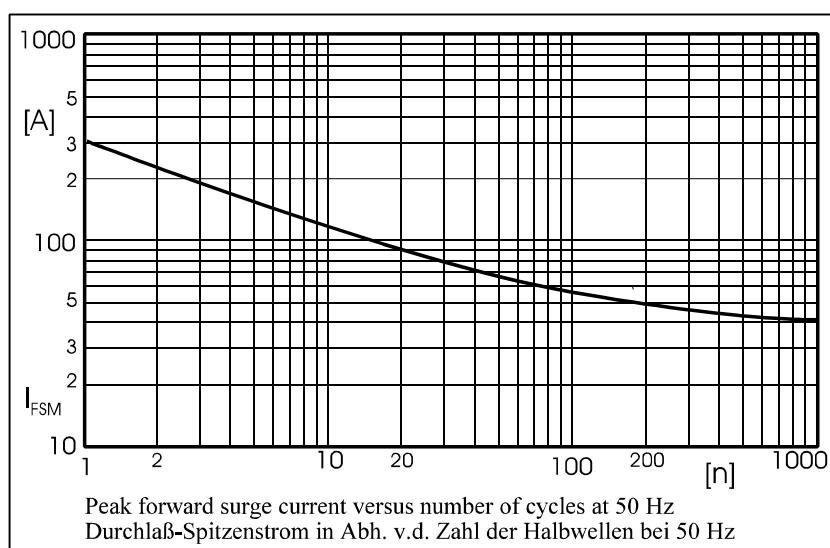
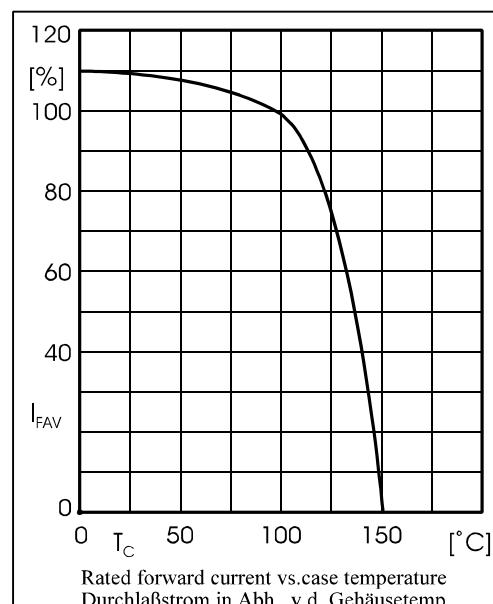
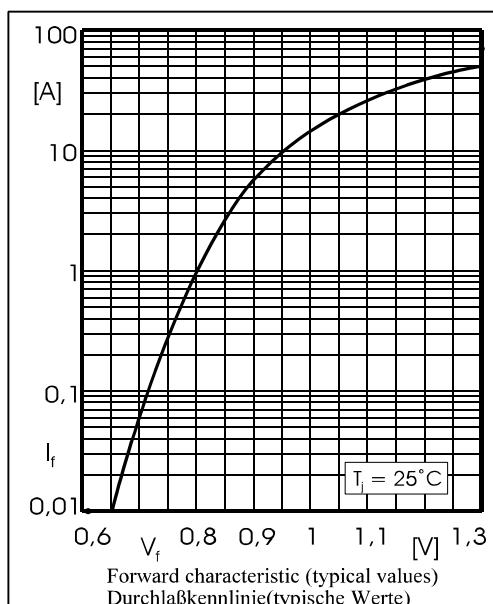
 Isolation voltage – Isolationsspannung $t = 1 \text{ min}$ V_{ISO} > 2000 V

 Operating junction temperature – Sperrschiitttemperatur
 Storage temperature – Lagerungstemperatur T_j – 50...+150/C T_s – 50...+150/C
¹⁾ Valid per diode – Gültig pro Diode

²⁾ Max. case temperature $T_c = 100/C$ – Max. Gehäusetemperatur $T_c = 100/C$

Characteristics**Kennwerte**

Max. current with cooling fin 300 cm ² Dauergrenzstrom mit Kühlblech 300 cm ²	$T_A = 50/\text{C}$	R-load C-load	I_{FAV} I_{FAV}	30.0 A 26.0 A
Forward voltage – Durchlaßspannung	$T_j = 25/\text{C}$	$I_F = 15 \text{ A}$	V_F	< 1.05 V ¹⁾
Leakage current – Sperrstrom	$T_j = 25/\text{C}$	$V_R = V_{RRM}$	I_R	< 25 : A
Thermal resistance junction to case Wärmewiderstand Sperrsicht – Gehäuse			R_{thC}	< 1.0 K/W
Admissible torque for mounting Zulässiges Anzugsdrehmoment		10-32 UNF M 5		18 ± 10% lb.in. 2 ± 10% Nm



¹⁾ Valid per diode – Gültig pro Diode